

$V_{DSS}$	1200V
$R_{DS(on)}$ (Typ.)	80mΩ
$I_D$	31A
$P_D$	165W

#### ●Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating ; RoHS compliant

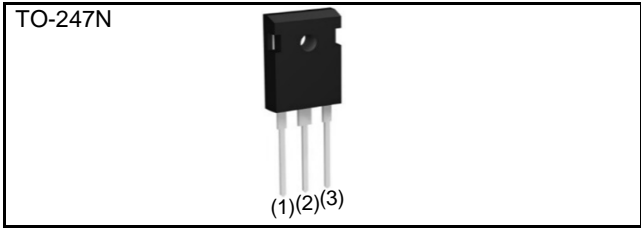
#### ●Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

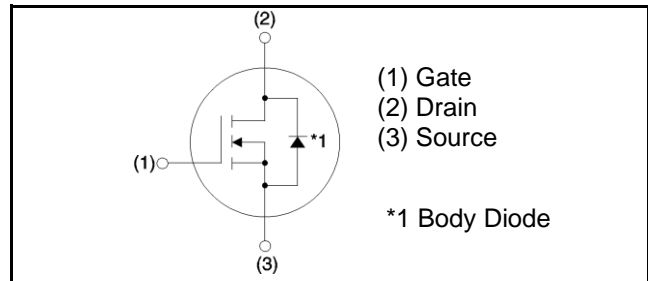
#### ●Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit	
Drain - Source voltage	$V_{DSS}$	1200	V	
Continuous drain current	$T_c = 25^\circ\text{C}$	$I_D^{*1}$	31	A
	$T_c = 100^\circ\text{C}$	$I_D^{*1}$	22	A
Pulsed drain current	$I_{D,pulse}^{*2}$	77	A	
Gate - Source voltage (DC)	$V_{GSS}$	-4 to +22	V	
Gate-Source Surge Voltage ( $t_{surge} < 300\text{nsec}$ )	$V_{GSS,surge}^{*3}$	-4 to +26	V	
Recommended Drive Voltage	$V_{GS,op}^{*4}$	0 / +18	V	
Junction temperature	$T_j$	175	$^\circ\text{C}$	
Range of storage temperature	$T_{stg}$	-55 to +175	$^\circ\text{C}$	

#### ●Outline



#### ●Inner circuit



#### ●Packaging specifications

Type	Packing	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	30
	Taping code	C11
	Marking	SCT3080KL

## ●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	$R_{thJC}$	-	0.70	0.91	°C/W

●Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	1200	-	-	V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 1200V, V_{GS} = 0V$ $T_j = 25^\circ\text{C}$	-	1	10	$\mu\text{A}$
		$T_j = 150^\circ\text{C}$	-	2	-	
Gate - Source leakage current	$I_{GSS+}$	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	$I_{GSS-}$	$V_{GS} = -4V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 5mA$	2.7	-	5.6	V
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = 18V, I_D = 10A$ $T_j = 25^\circ\text{C}$	-	80	104	$\text{m}\Omega$
		$T_j = 125^\circ\text{C}$	-	120	-	
Gate input resistance	$R_G$	$f = 1\text{MHz}, \text{open drain}$	-	12	-	$\Omega$

**●Electrical characteristics (T<sub>a</sub> = 25°C)**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Transconductance	$g_{fs}^{*5}$	$V_{DS} = 10V, I_D = 10A$	-	4.4	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0V$	-	785	-	pF
Output capacitance	$C_{oss}$	$V_{DS} = 800V$	-	75	-	
Reverse transfer capacitance	$C_{rss}$	$f = 1MHz$	-	35	-	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 600V$	-	74	-	pF
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} = 400V, I_D = 10A$	-	15	-	ns
Rise time	$t_r^{*5}$	$V_{GS} = 18V/0V$	-	22	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 40\Omega$	-	29	-	
Fall time	$t_f^{*5}$	$R_G = 0\Omega$	-	24	-	
Turn - on switching loss	$E_{on}^{*5}$	$V_{DD} = 600V, I_D = 10A$ $V_{GS} = 18V/0V$ $R_G = 0\Omega, L = 750\mu H$	-	132	-	$\mu J$
Turn - off switching loss	$E_{off}^{*5}$	* $E_{on}$ includes diode reverse recovery	-	18	-	

**●Gate Charge characteristics (T<sub>a</sub> = 25°C)**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	$Q_g^{*5}$	$V_{DD} = 600V$	-	60	-	nC
Gate - Source charge	$Q_{gs}^{*5}$	$I_D = 10A$	-	15	-	
Gate - Drain charge	$Q_{gd}^{*5}$	$V_{GS} = 18V$	-	25	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 600V, I_D = 10A$	-	9.6	-	V

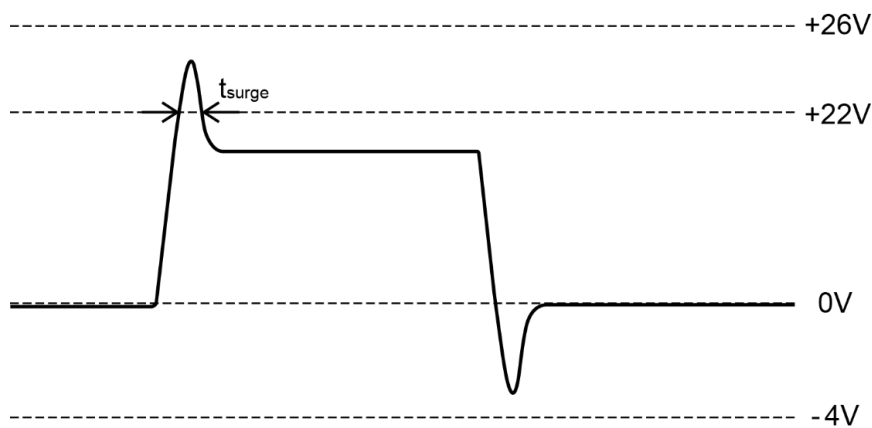
**●Body diode electrical characteristics (Source-Drain) ( $T_a = 25^\circ\text{C}$ )**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	$I_S$ *1	$T_c = 25^\circ\text{C}$	-	-	31	A
Inverse diode direct current, pulsed	$I_{SM}$ *2		-	-	77	A
Forward voltage	$V_{SD}$ *5	$V_{GS} = 0\text{V}, I_S = 10\text{A}$	-	3.2	-	V
Reverse recovery time	$t_{rr}$ *5	$I_F = 10\text{A}, V_R = 600\text{V}$ $di/dt = 1100\text{A}/\mu\text{s}$	-	17	-	ns
Reverse recovery charge	$Q_{rr}$ *5		-	50	-	nC
Peak reverse recovery current	$I_{rrm}$ *5		-	6	-	A

\*1 Limited only by maximum temperature allowed.

\*2  $PW \leq 10\mu\text{s}$ , Duty cycle  $\leq 1\%$

\*3 Example of acceptable Vgs waveform



\*4 Please be advised not to use SiC-MOSFETs with  $V_{gs}$  below 13V as doing so may cause thermal runaway.

\*5 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

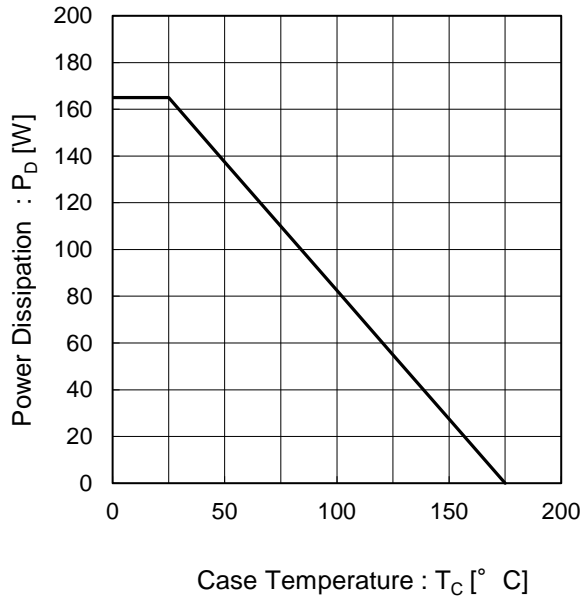


Fig.2 Maximum Safe Operating Area

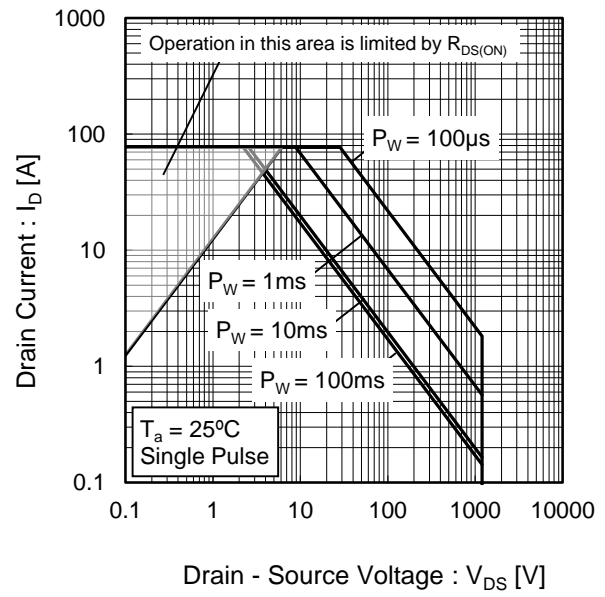
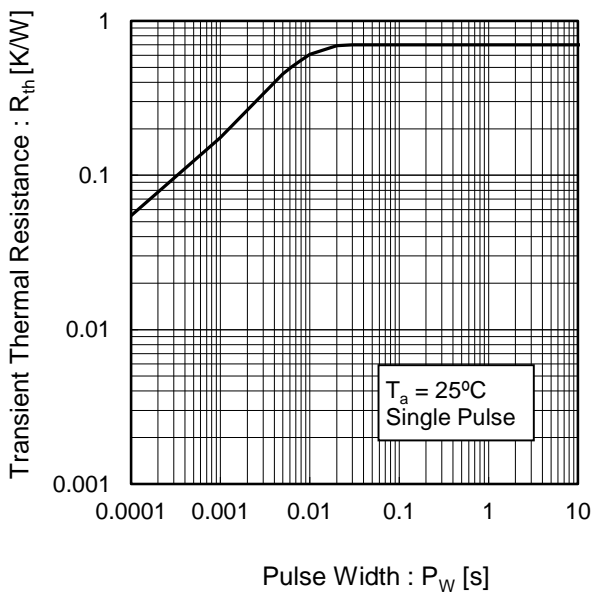


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

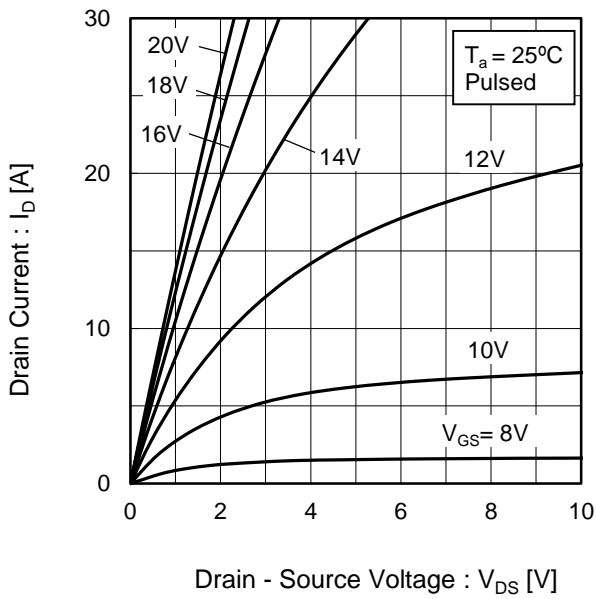


Fig.5 Typical Output Characteristics(II)

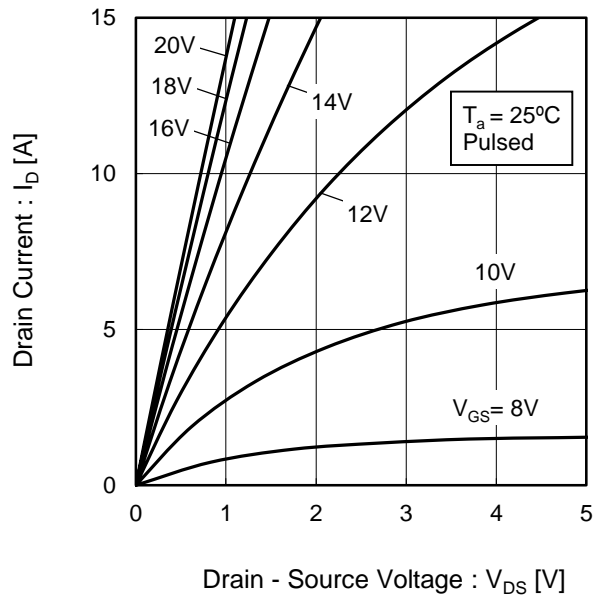


Fig.6  $T_j = 150^\circ\text{C}$  Typical Output Characteristics(I)

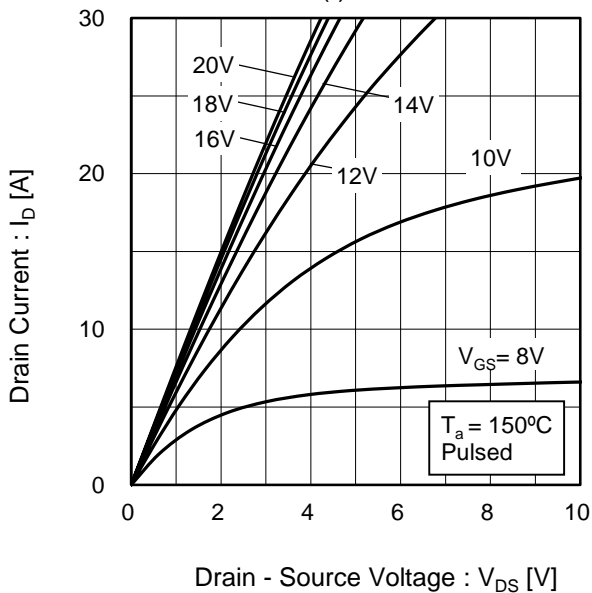
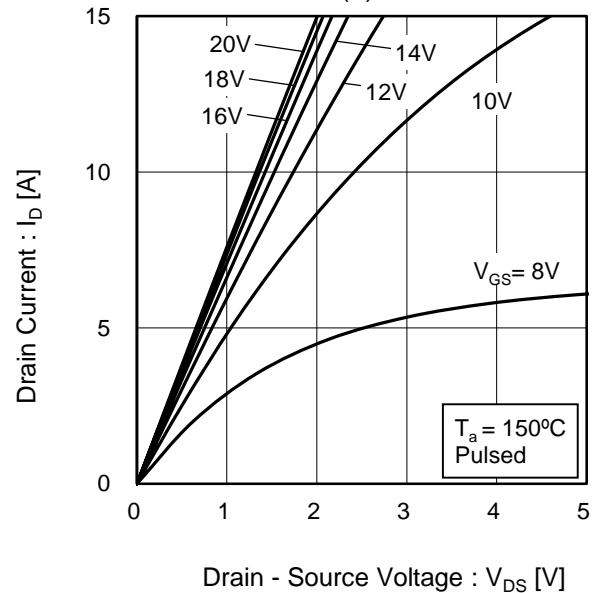


Fig.7  $T_j = 150^\circ\text{C}$  Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics (I)

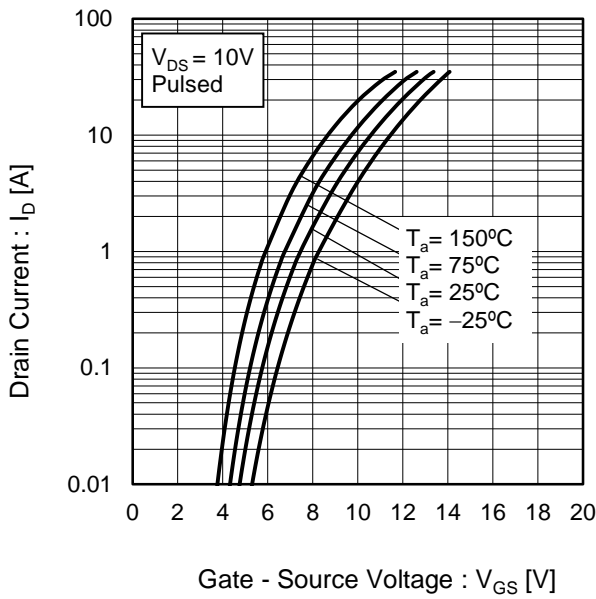


Fig.9 Typical Transfer Characteristics (II)

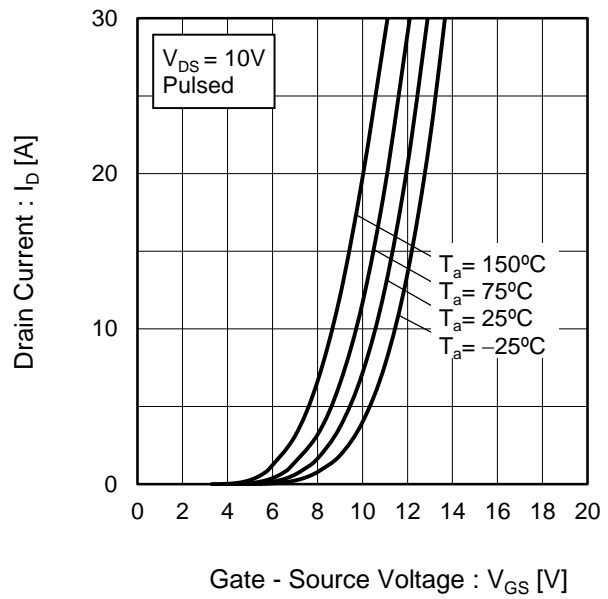


Fig.10 Gate Threshold Voltage vs. Junction Temperature

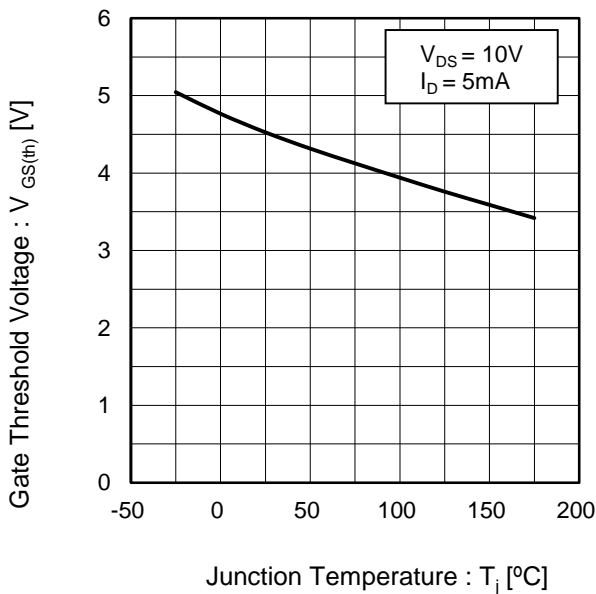
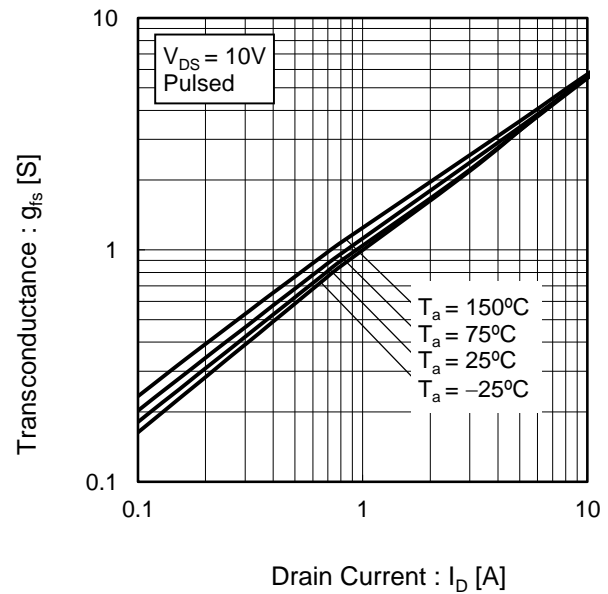


Fig.11 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

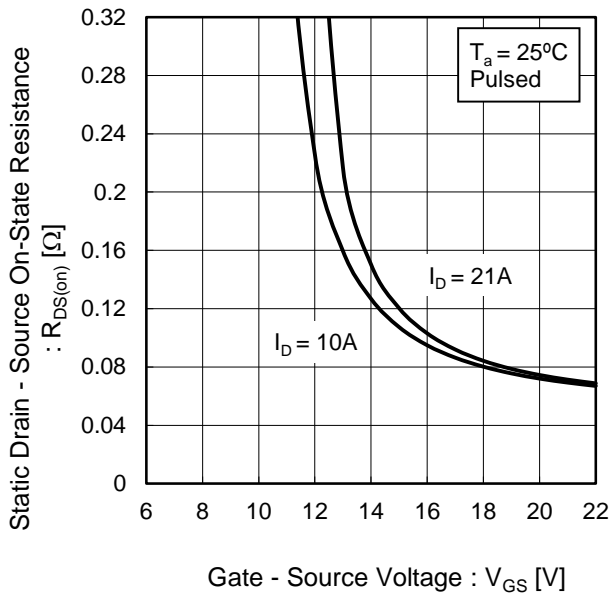


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

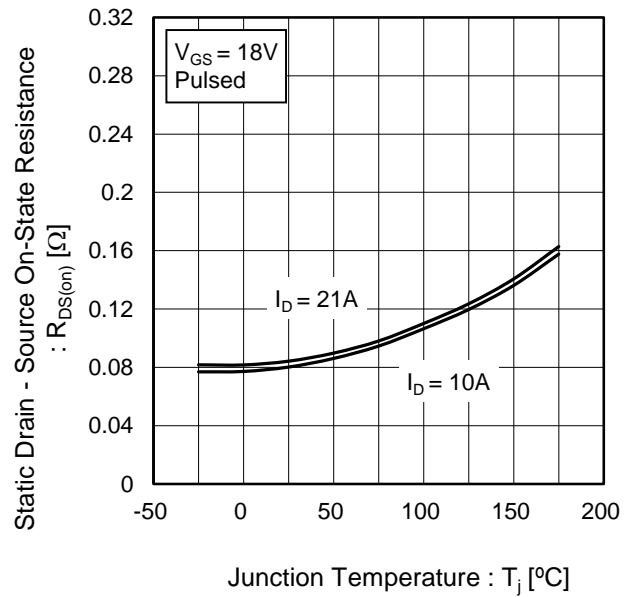
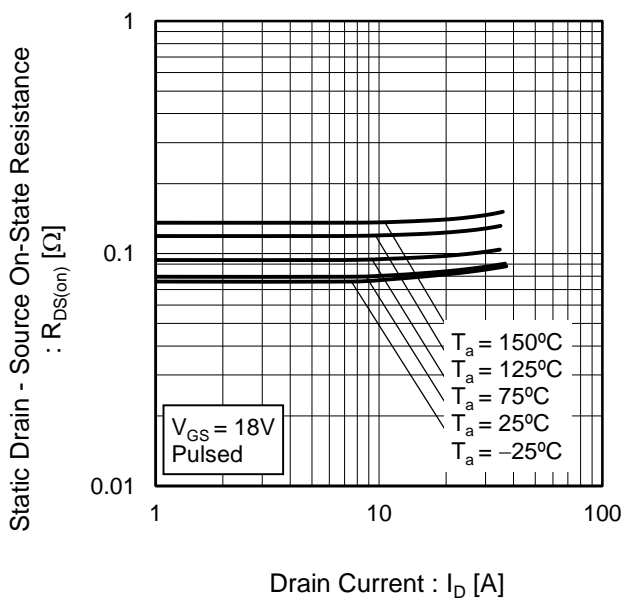


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current





●Electrical characteristic curves

Fig.15 Typical Capacitance vs. Drain - Source Voltage

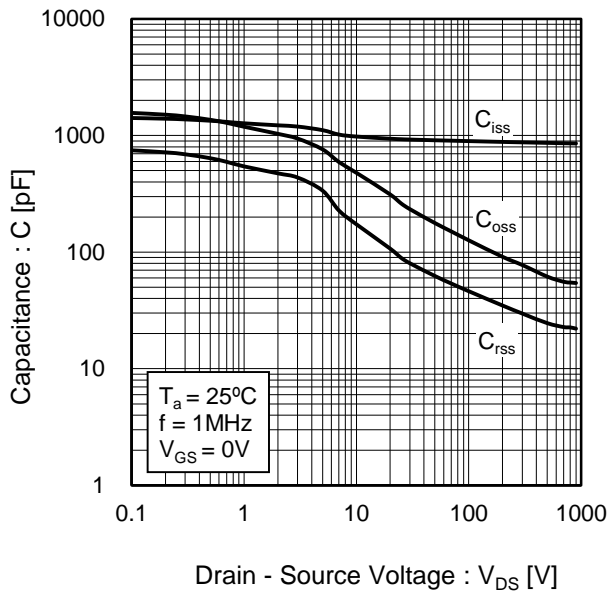


Fig.16 Coss Stored Energy

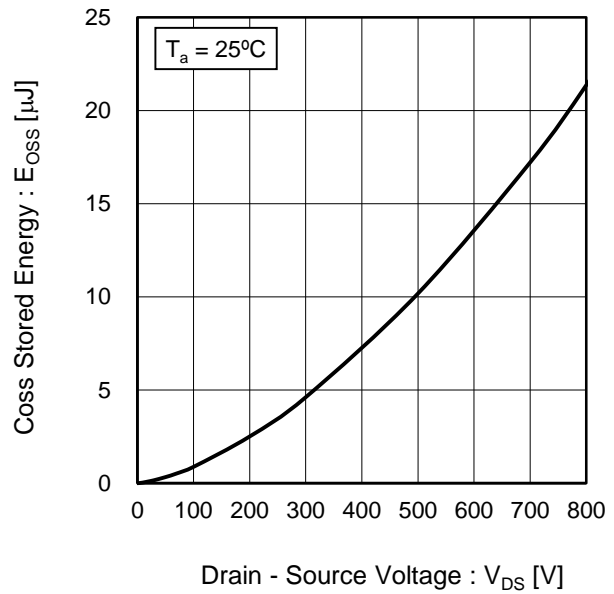


Fig.17 Switching Characteristics

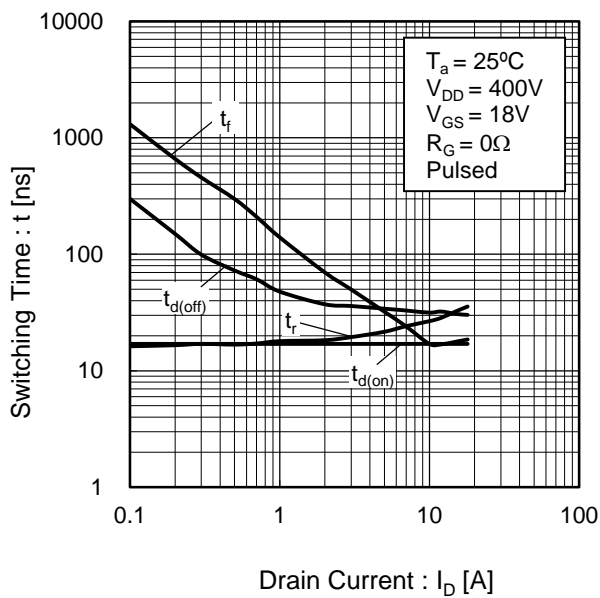
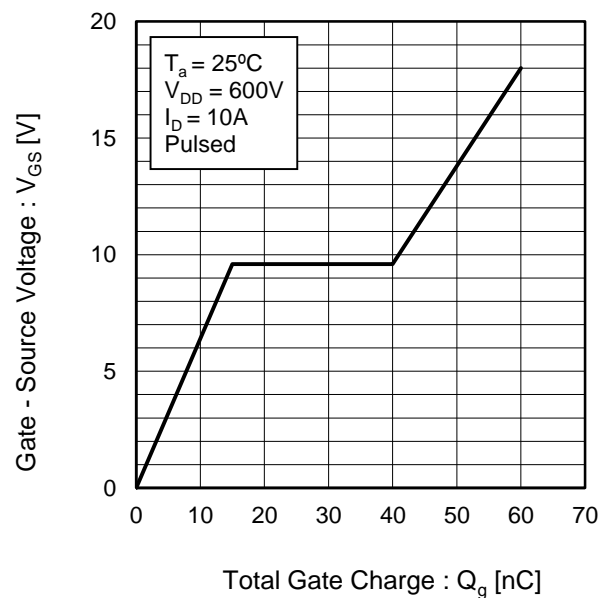


Fig.18 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.19 Typical Switching Loss vs. Drain - Source Voltage

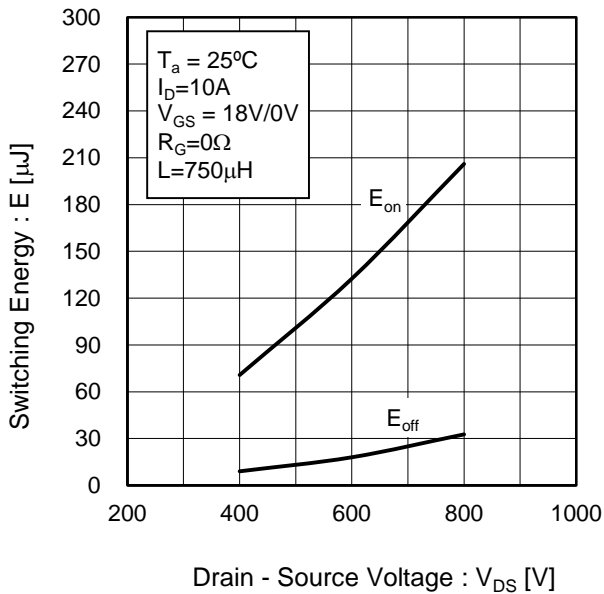


Fig.20 Typical Switching Loss vs. Drain Current

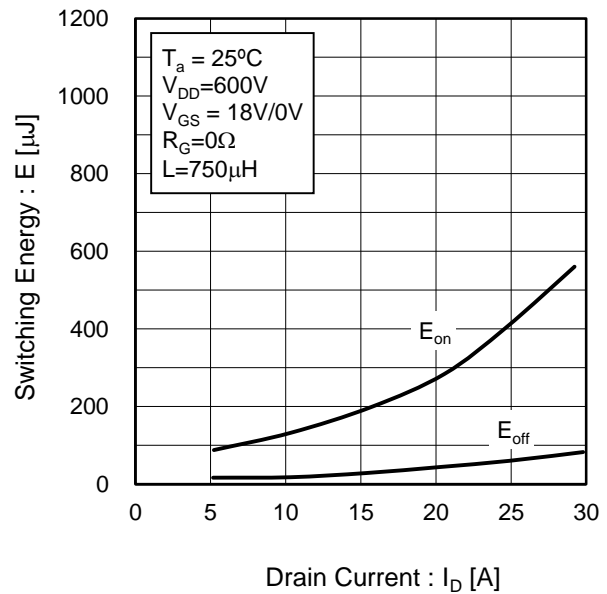
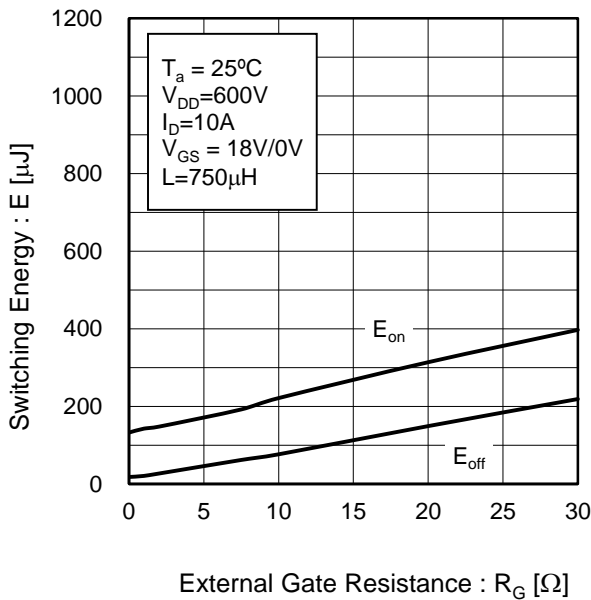


Fig.21 Typical Switching Loss vs. External Gate Resistance



●Electrical characteristic curves

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

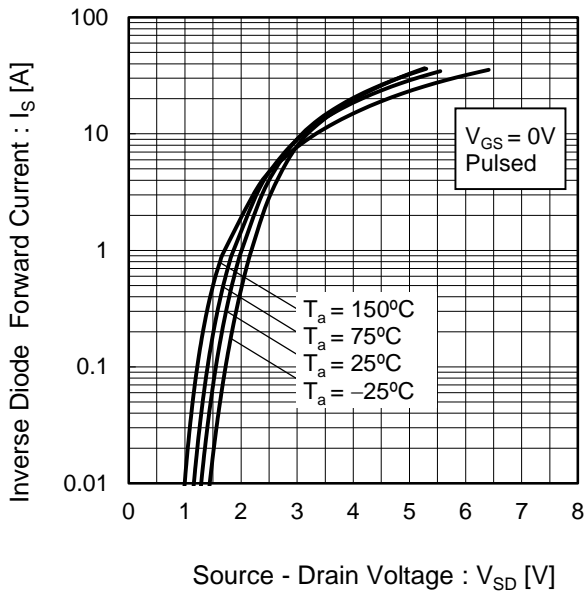
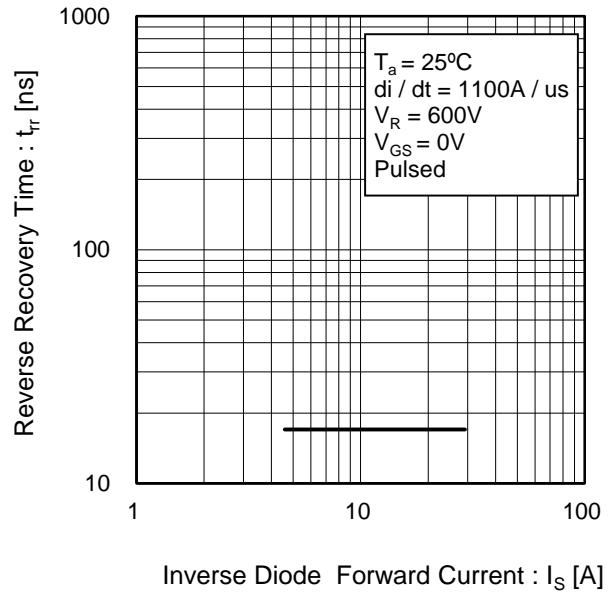


Fig.23 Reverse Recovery Time vs. Inverse Diode Forward Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

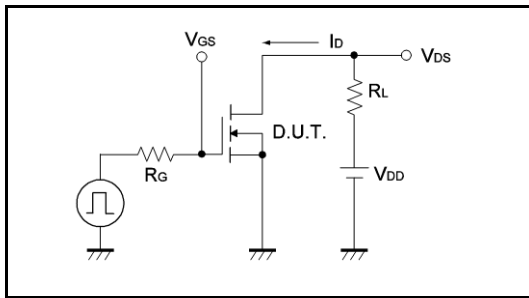


Fig.1-2 Switching Waveforms

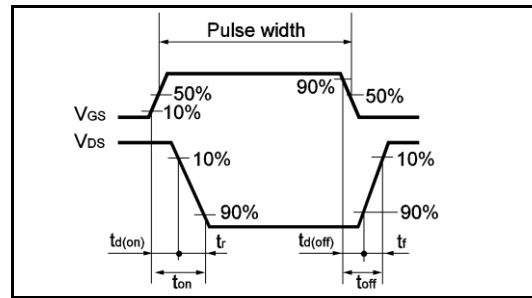


Fig.2-1 Gate Charge Measurement Circuit

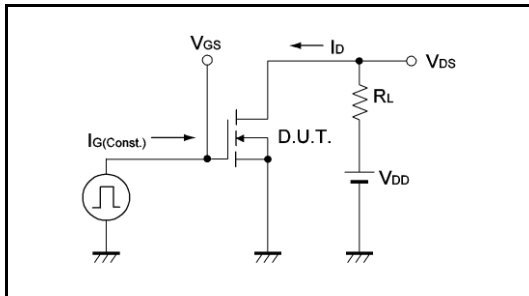


Fig.2-2 Gate Charge Waveform

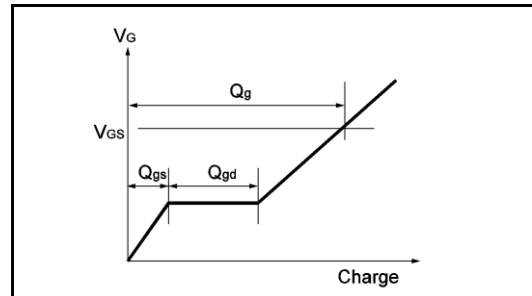


Fig.3-1 Switching Energy Measurement Circuit

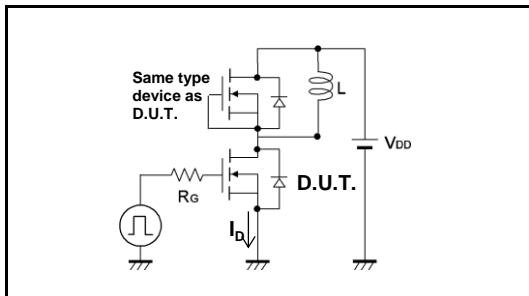


Fig.3-2 Switching Waveforms

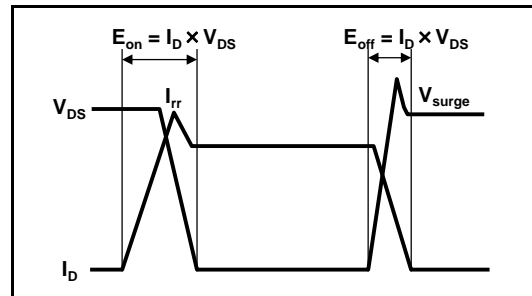


Fig.4-1 Reverse Recovery Time Measurement Circuit

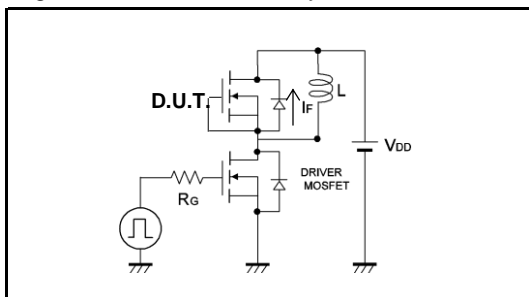
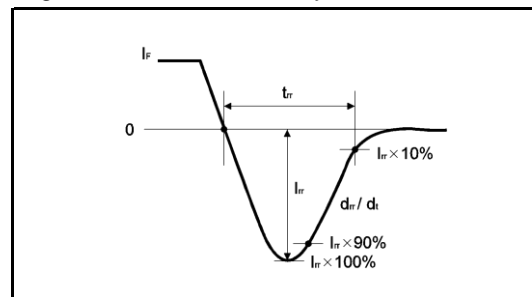


Fig.4-2 Reverse Recovery Waveform



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